

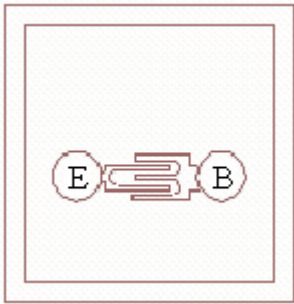
9018 Silicon NPN Epitaxial Transistor

Description :The 9018 is designed for UHF general amplifier applications

Features: ●Excellent h_{FE} Linearity

●Excellent f_T characteristic

Chip Appearance

	Chip Size		360um × 360um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	φ 65um
		Emitter	φ 65um
	Front Metal		AlSiCu
	Backside Metal		Au (As)
	Scribe line width		50um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$		0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=3V, I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=0.1mA$	30		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA$	20		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=0.1mA$	5		V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=1mA$	60	200	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$		0.3	V